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< Silicon Rf Power MOS FET (Discrete) > RD07MVS1 RoHS Compliant, Silicon MOSFET Power Transistor, 175MHz, 520MHz, 7W DESCRIPTION RD07MVS1 is a MOS FET type transistor specifically designed for VHF/UHF RF power amplifiers applications. FEATURES High power gain: Pout>7W, Gp>10dB@Vdd=7.2V, f=520MHz High Efficiency: 60%typ. (175MHz) High Efficiency: 55 ...

Silicon MOSFET RF Power Transistors - MACOM

< Silicon Rf Power MOS FET (Discrete) > RD02MUS2 RoHS Compliance, Silicon MOSFET Power Transistor 175MHz, 520MHz, 2W DESCRIPTION RD02MUS2 is a MOS FET type transistor specifically designed for V HF/U RF power amplifiers applications. This device has an internal monolithic zener diode from gate to source for ESD protection. FEATURES •High power gain:

STMicroelectronics Silicon Carbide Power MOSFETs ...

A silicon carbide MOSFET was first created by Wolfspeed about 20 years ago. Compared to silicon MOSFETs, these MOSFETs provide higher temperature operation, an increased critical breakdown strength (10x that of silicon), higher switching frequencies, and reduced switching losses.

< Silicon Rf Power MOS FET (Discrete) > RD01MUS2B RoHS Compliance, Silicon MOSFET Power Transistor 527MHz, 1W DESCRIPTION RD01MUS2B is a MOS FET type transistor specifically designed for VHF/UHF RF amplifiers applications. This device has an internal monolithic zener diode from gate to source for ESD protection. FEATURES

What is a Silicon Carbide MOSFET | Wolfspeed

10 March, 2020 CISSOID announces 3-Phase SiC MOSFET Intelligent Power Module for E-mobility 20 December, 2019 STMicroelectronics TCPP01-M12 USB Type-C Port Protection 15 November, 2019 CoolSiC™ MOSFET evaluation board for motor drives up to 7.5 kW

Silicon RF Power MOSFET | Products & Suppliers ...

4H-SiC RF power MOSFETs - ResearchGate

Silicon (Si) power metal-oxide-semiconductor field-effect transistors (MOSFETs) are widely used in audio and radio frequency (rf) amplifiers, switch mode power supplies (SMPS), power factor ...

< Silicon RF Power MOS FET (Discrete) > RD07MVS1

The deployment of digital networks has required migration to multi-carrier RF power amplifiers with stringent demands on linearity and efficiency. This book describes the physics, design considerations and RF performance of silicon power Metal-Oxide- Semiconductor Field Effect Transistors (MOSFETs) that are at the heart of the power amplifiers.

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< Silicon RF Power MOS FET (Discrete) > RD02MUS2

< Silicon Rf Power MOS FET (Discrete) > RD16HHF1 RoHS Compliance, Silicon MOSFET Power Transistor 30MHz, 16W DESCRIPTION RD16HHF1 is a MOS FET type transistor specifically designed for HF RF power amplifiers applications. FEATURES High power gain: Pout>16W, Gp>16dB @Vd-s=12.5V, f=30MHz Integrated gate protection diode APPLICATION

Mitsubishi Silicon RF devices support wireless communication networks. Mitsubishi Silicon RF devices which are the key parts for amplifying power of the transmission stage of mobile wireless communication devices in the high frequency band from several MHz to 1GHz robustly support wireless communication networks with a wide range of product lineup such as mobile professional

radio equipment ...

< Silicon RF Power MOS FET (Discrete) > RD16HHF1

TT Electronics' range of RF power MOSFETs is one of the widest available and includes over 100 devices including D2254UK. There is a device for almost any application - from low cost to ultrahigh performance, from 750mW to over 400W, and for frequencies to 1GHz. Parts for 12.5V, 28V and 50V are available in both single-ended and push-pull formats.

< Silicon RF Power MOS FET (Discrete) > RD01MUS2B

RF Power MOSFETs | Products | D2254UK | TT Electronics

Silicon Rf Power Mos Fet

RF Power Transistors - Silicon MOSFET At MACOM we offer a broad range of TMOS and DMOS RF power MOSFET transistor products as discrete devices from DC to 1.0 GHz. Our high power MOS-FET transistors are ideal for civil avionics, communications, networks, radar, and industrial, scientific, and medical applications.

Silicon MOSFET RF Power Transistors - MACOM

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< Silicon RF Power MOS FET (Discrete) > RD16HHF1

< Silicon Rf Power MOS FET (Discrete) > RD01MUS3 RoHS Compliant, 2-stage Silicon MOSFET Power Transistor VHF/UHF/940MHz, 1W, 7.2V Description RD01MUS3 is a 2-stage MOSFET transistor for RF driver device. Designed for specifically VHF/UHF/940MHz-band RF power amplifiers applications. FEATURES High power gain and High Efficiency.

< Silicon RF Power MOS FET (Discrete) > RD01MUS3

Description: RF Power Vertical MOSFET. The VRF161 is a gold-metallized silicon n-channel RF power transistor designed for broadband commercial and military applications requiring high power and gain without compromising reliability, ruggedness, or inter-modulation. Operating Frequency: 150 MHz; Output Power: 200 watts; Power Gain: 24 dB

Silicon RF Power MOSFET | Products & Suppliers ...

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RF Power MOSFETs | Products | D2254UK | TT Electronics

RF silicon MOSFET power transistor, 12.5V, 75W, 20A MITSUBISHI RD70HVF1

RD70HVF1 MITSUBISHI | RF silicon MOSFET power transistor ...

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RF Power MOSFETs | Products | D2081UK | TT Electronics

RD100HHF1 is a MOS FET type transistor specifically designed for HF High power amplifiers applications. High power and High Gain: Pout>100W, Gp>11.5dB @Vdd=12.5V, f=30MHz High Efficiency: 60%typ.on HF Band. For output stage of high power amplifiers in HF Band mobile radio sets. RD100HHF1-101 is a RoHS compliant products.

RD100HHF1 Mitsubishi MOSFET Silicon Power Transistor 30MHz ...

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Silicon RF Devices - Mitsubishi Electric

Part Name Description ; F1007/PF : 4A, 70V, RF N-Channel MOSFET. F1008/PF : 8A, 70V, N-Channel RF Power MOSFET. F1020/PF

RF MOSFET | PSpice

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CC-MOSFET RF Performance. CC-MOSFET Thermal Effects. GD-MOSFET Structure. GD-MOSFET Blocking Characteristics. GD-MOSFET On-State Characteristics. GD-MOSFET Output and Transfer Characteristics. ... Silicon RF Power MOSFETs. Metrics. Downloaded 11 times History. Loading ... Close Figure ...

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< Silicon RF Power MOS FET (Discrete) > RD01MUS3

RD70HVF1 MITSUBISHI | RF silicon MOSFET power transistor ...

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